



7N70K-MTQ

Preliminary

Power MOSFET

7A, 700V N-CHANNEL POWER MOSFET

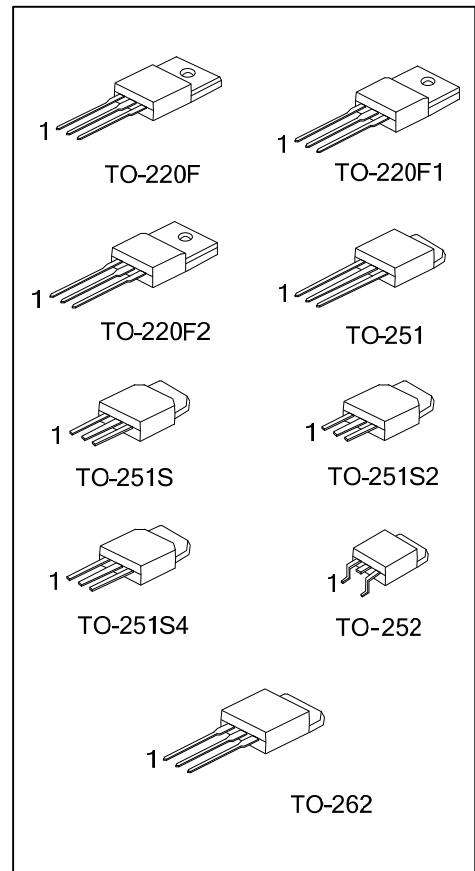
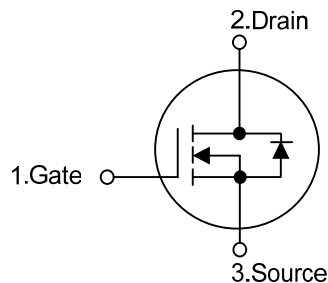
DESCRIPTION

The UTC 7N70K-MTQ is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 1.7\Omega$ @ $V_{GS} = 10V$, $I_D = 3.5A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



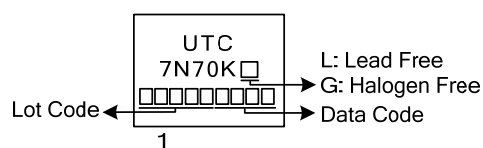
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
7N70KL-TF3-T	7N70KG-TF3-T	TO-220F	G	D	S	Tube
7N70KL-TF1-T	7N70KG-TF1-T	TO-220F1	G	D	S	Tube
7N70KL-TF2-T	7N70KG-TF2-T	TO-220F2	G	D	S	Tube
7N70KL-TM3-T	7N70KG-TM3-T	TO-251	G	D	S	Tube
7N70KL-TMS-T	7N70KG-TMS-T	TO-251S	G	D	S	Tube
7N70KL-TMS2-T	7N70KG-TMS2-T	TO-251S2	G	D	S	Tube
7N70KL-TMS4-T	7N70KG-TMS4-T	TO-251S4	G	D	S	Tube
7N70KL-TN3-R	7N70KG-TN3-R	TO-252	G	D	S	Tape Reel
7N70KL-T2Q-T	7N70KG-T2Q-T	TO-262	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

7N70KG-TF3-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2 TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2 TMS4: TO-251S4, TN3: TO-252, T2Q: TO-262 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	7.0	A
	Pulsed (Note 2)	I_{DM}	28	A
Avalanche Current (Note 2)		I_{AR}	6.4	A
Avalanche Energy		E_{AS}	205	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220F/TO-220F1 TO-220F2	P_D	48	W
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252		57	W
	TO-262		142	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 10\text{mH}$, $I_{AS} = 6.4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 7.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F/TO-220F1 TO-220F2/TO-262	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252		110	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F/TO-220F1	θ_{JC}	2.6	$^\circ\text{C}/\text{W}$
	TO-220F2		2.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252		2.2	$^\circ\text{C}/\text{W}$
	TO-262		0.88	$^\circ\text{C}/\text{W}$

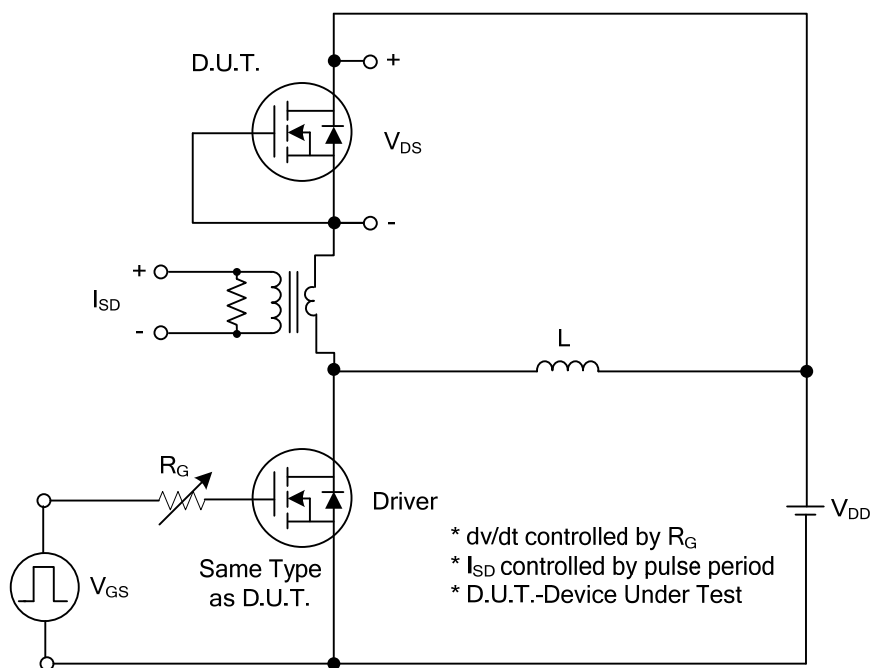
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	700			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 700V, V _{GS} = 0V			1	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Drain-Source ON-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D = 3.5A			1.7	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		480		pF
Output Capacitance		C _{OSS}			80		pF
Reverse Transfer Capacitance		C _{RSS}			6.5		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q _G	V _{DS} = 50V,I _D = 1.3A, V _{GS} = 10V (Note 1, 2)		21.8		nC
Gate to Source Charge		Q _{GS}			6.8		nC
Gate to Drain Charge		Q _{DD}			4.8		nC
Turn-on Delay Time (Note 1)		t _{D(ON)}	V _{DD} = 30V, I _D = 0.5A, R _G = 25Ω (Note 1, 2)		57		ns
Rise Time		t _R			60		ns
Turn-off Delay Time		t _{D(OFF)}			128		ns
Fall-Time		t _F			52		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				7.0	A
Maximum Body-Diode Pulsed Current		I _{SM}				28	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =7.0A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)		t _{rr}	I _S =7.0A, V _{GS} =0V,		320		ns
Reverse Recovery Charge		Q _{rr}	dl _F /dt =100A/μs		2.4		μC

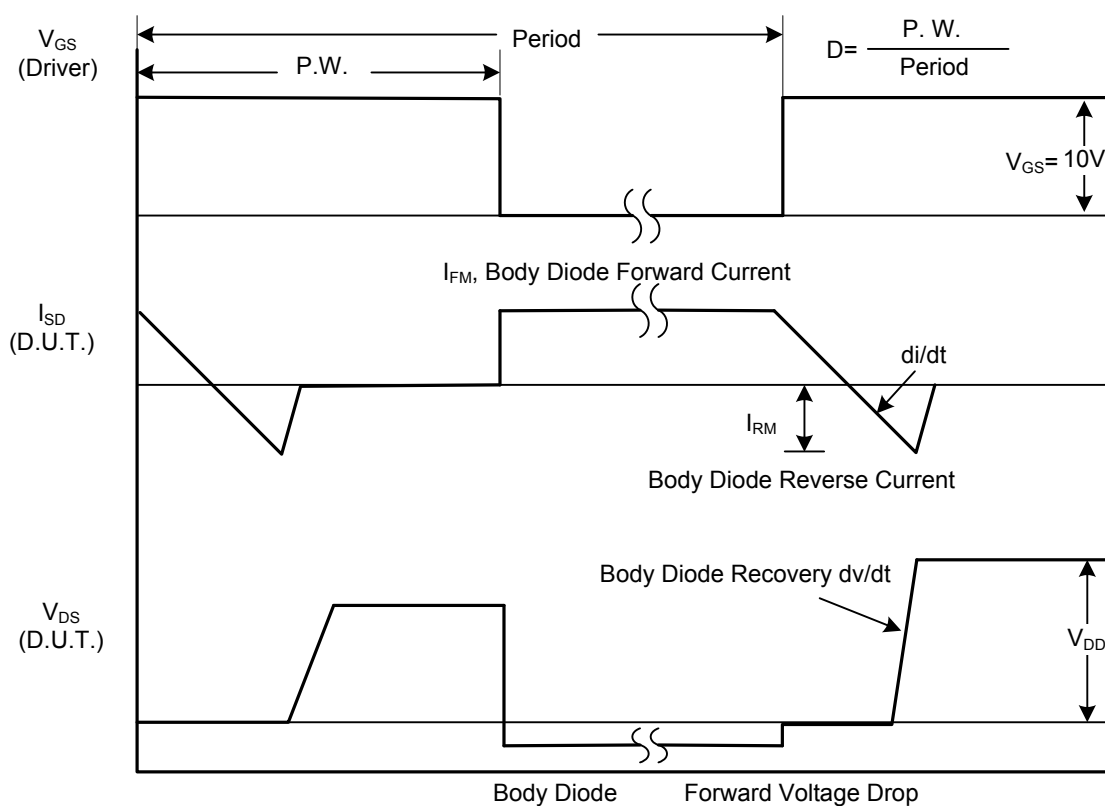
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

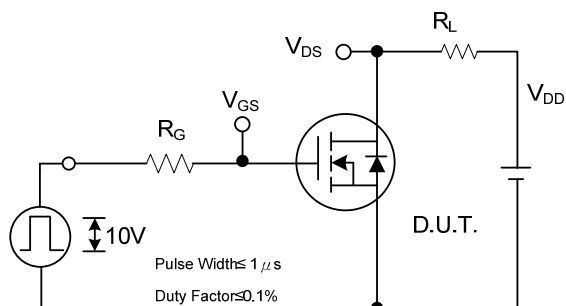


Peak Diode Recovery dv/dt Test Circuit

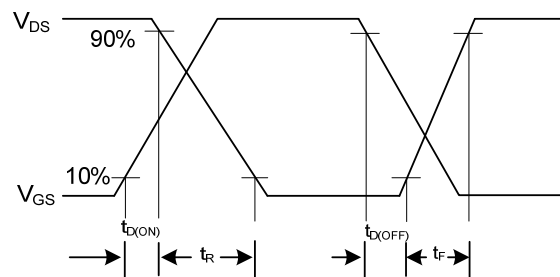


Peak Diode Recovery dv/dt Waveforms

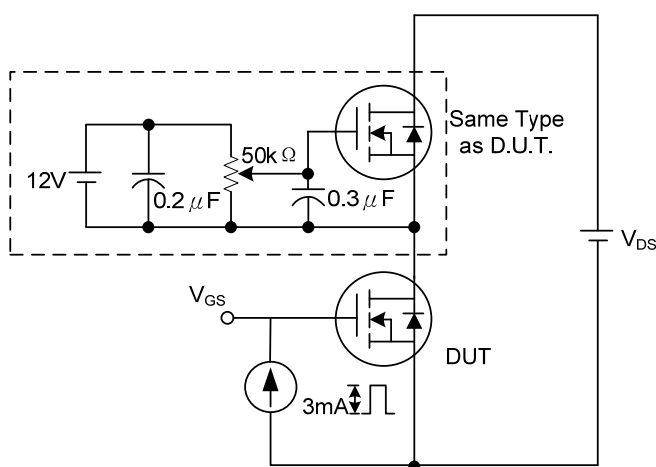
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



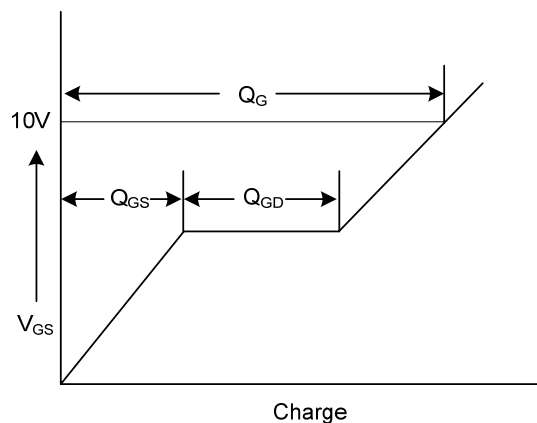
Switching Test Circuit



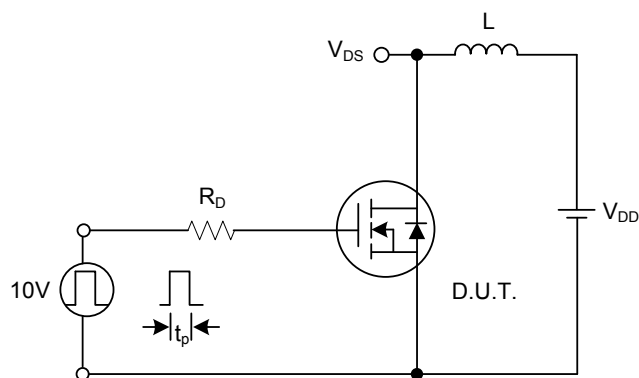
Switching Waveforms



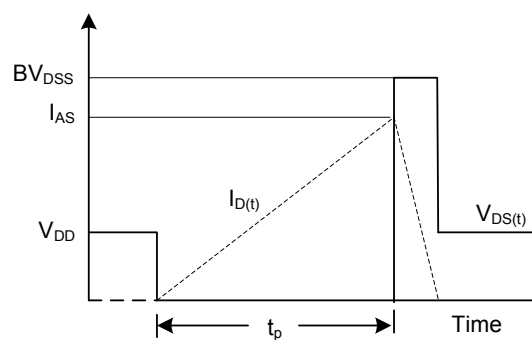
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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